



CD4023M/CD4023C Triple 3-Input NAND Gate CD4025M/CD4025C Triple 3-Input NOR Gate

General Description

These triple gates are monolithic complementary MOS (CMOS) integrated circuits constructed with N- and P-channel enhancement mode transistors. All inputs are protected against static discharge with diodes to V_{DD} and V_{SS} .

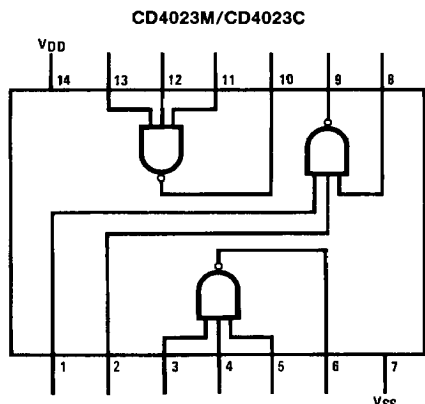
Features

- Wide supply voltage range
- High noise immunity
- 5V–10V parametric ratings
- Low power

3.0V to 15V
0.45 V_{DD} (typ.)

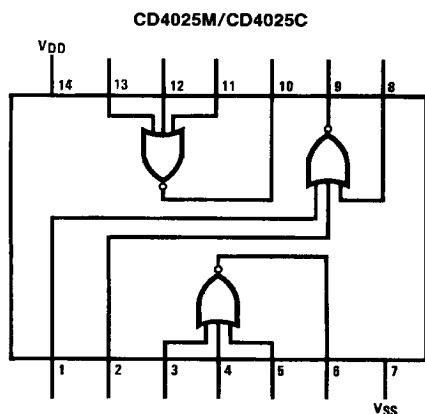
Connection Diagrams

Dual-In-Line Packages



Top View

TL/F/5955-1



Top View

TL/F/5955-2

Order Number CD4023* or CD4025*

*Please look into Section 8, Appendix D for availability of various package types.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required,
contact the National Semiconductor Sales Office/
Distributors for availability and specifications.

Voltage at Any Pin $V_{SS} -$ to $V_{DD} + 0.3V$

Operating Temperature Range

CD4023M, CD4025M $-55^{\circ}C$ to $+125^{\circ}C$

CD4023C, CD4025C $-40^{\circ}C$ to $+85^{\circ}C$

Storage Temperature Range

$-65^{\circ}C$ to $+150^{\circ}C$

Power Dissipation (P_D)

Dual-In-Line 700 mW

Small Outline 500 mW

Operating V_{DD} Range

$V_{SS} + 3.0V$ to $V_{SS} + 15V$

Lead Temperature

(Soldering, 10 seconds) $260^{\circ}C$

DC Electrical Characteristics CD4023M, CD4025M

Symbol	Parameter	Conditions	Limits							Units
			- 55°C		+ 25°C			+ 125°C		
			Min	Max	Min	Typ	Max	Min	Max	
I _L	Quiescent Device Current	V _{DD} = 5.0V V _{DD} = 10V		0.05 0.1		0.001 0.001	0.05 0.1		3.0 6.0	μA μA
P _D	Quiescent Device Dissipation/Package	V _{DD} = 5.0V V _{DD} = 10V		0.25 1.0		0.005 0.01	0.25 1.0		15 60	μW μW
V _{OL}	Output Voltage Low Level	V _{DD} = 5.0V, V _I = V _{DD} , I _O = 0A V _{DD} = 10V, V _I = V _{DD} , I _O = 0A		0.05 0.05		0 0	0.05 0.05		0.05 0.05	V V
V _{OH}	Output Voltage High Level	V _{DD} = 5.0V, V _I = V _{SS} , I _O = 0A V _{DD} = 10V, V _I = V _{SS} , I _O = 0A	4.95 9.95		4.95 9.95	5.0 10		4.95 9.95		V V
V _{NL}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O = 3.6V, I _O = 0A V _{DD} = 10V, V _O = 7.2V, I _O = 0A	1.5 3.0		1.5 3.0	2.25 4.5		1.4 2.9		V V
V _{NH}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O = 0.95V, I _O = 0A V _{DD} = 10V, V _O = 2.9V, I _O = 0A	1.4 2.9		1.5 3.0	2.25 4.5		1.5 3.0		V V
I _{DN}	Output Drive Current N-Channel (4025) (Note 2)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD} V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	0.5 1.1		0.40 0.9	1.0 2.5		0.28 0.65		mA mA
I _{DP}	Output Drive Current P-Channel (4025) (Note 2)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS} V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	-0.62 -0.62		-0.5 -0.5	-2.0 -1.0		-0.35 -0.35		mA mA
I _{DN}	Output Drive Current N-Channel (4023) (Note 2)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD} V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	0.31 0.63		0.25 0.5	0.5 0.6		0.175 0.35		mA mA
I _{DP}	Output Drive Current P-Channel (4023) (Note 2)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS} V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	-0.31 -0.75		-0.25 -0.6	-0.5 -1.2		-0.175 -0.4		mA mA
I _I	Input Current					10				pA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Recommended Operating Conditions" and "Electrical Characteristics" provide conditions for actual device operation.

Note 2: I_{DN} and I_{DP} are tested one output at a time.

DC Electrical Characteristics CD4023C, CD4025C

Symbol	Parameter	Conditions	Limits							Units
			−40°C		+ 25°C			+ 85°C		
			Min	Max	Min	Typ	Max	Min	Max	
I _L	Quiescent Device Current	V _{DD} = 5.0V V _{DD} = 10V		0.05 5.0		0.005 0.005	0.5 5.0		15 30	μA μA
P _D	Quiescent Device Dissipation/Package	V _{DD} = 5.0V V _{DD} = 10V		2.5 50		0.025 0.05	2.5 50		75 300	μW μW
V _{OL}	Output Voltage Low Level	V _{DD} = 5.0V, V _I = V _{DD} , I _O = 0A V _{DD} = 10V, V _I = V _{DD} , I _O = 0A		0.01 0.01		0 0	0.01 0.01		0.05 0.05	V V
V _{OH}	Output Voltage High Level	V _{DD} = 5.0V, V _I = V _{SS} , I _O = 0A V _{DD} = 10V, V _I = V _{SS} , I _O = 0A	4.99 9.99		4.99 9.99	5.0 10		4.95 9.95		V V
I _I	Input Current					10				pA
V _{NL}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O = 3.6V, I _O = 0A V _{DD} = 10V, V _O = 7.2V, I _O = 0A	1.5 3.0		1.5 3.0	2.25 4.5		1.4 2.9		V V
V _{NH}	Noise Immunity (All Inputs)	V _{DD} = 5.0V, V _O = 0.95V, I _O = 0A V _{DD} = 10V, V _O = 2.9V, I _O = 0A	1.4 2.9		1.5 3.0	2.25 4.5		1.5 3.0		V V
I _{DN}	Output Drive Current N-Channel (4025) (Note 2)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD} V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	0.35 0.72		0.3 0.6	1.0 2.5		0.24 0.48		mA mA
I _{DP}	Output Drive Current P-Channel (4025) (Note 2)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS} V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	−0.35 −0.3		−0.3 −0.25	−2.0 −1.0		−0.24 −0.2		mA mA
I _{DN}	Output Drive Current N-Channel (4023) (Note 2)	V _{DD} = 5.0V, V _O = 0.4V, V _I = V _{DD} V _{DD} = 10V, V _O = 0.5V, V _I = V _{DD}	0.145 0.3		0.12 0.25	0.5 0.6		0.095 0.2		mA mA
I _{DP}	Output Drive Current P-Channel (4023) (Note 2)	V _{DD} = 5.0V, V _O = 2.5V, V _I = V _{SS} V _{DD} = 10V, V _O = 9.5V, V _I = V _{SS}	−0.145 −0.35		−0.12 −0.3	−0.5 −1.2		−0.095 −0.24		mA mA
I _I	Input Current					10				pA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Recommended Operating Conditions" and "Electrical Characteristics" provide conditions for actual device operation.

Note 2: I_{DN} and I_{DP} are tested one output at a time.

AC Electrical Characteristics* $T_A = 25^\circ\text{C}$, $C_L = 15\text{ pF}$, and input rise and fall times = 20 ns. Typical temperature coefficient for all values of $V_{DD} = 0.3\%/^\circ\text{C}$

Symbol	Parameter	Conditions	Min	Typ	Max	Units
CD4025M						
t_{PHL}	Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		35	50	ns
		$V_{DD} = 10\text{V}$		25	40	ns
t_{PLH}	Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		35	40	ns
		$V_{DD} = 10\text{V}$		25	70	ns
t_{THL}	Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		65	125	ns
		$V_{DD} = 10\text{V}$		35	70	ns
t_{TLH}	Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		65	175	ns
		$V_{DD} = 10\text{V}$		35	75	ns
C_i	Input Capacitance	Any Input		5.0		pF
CD4025C						
t_{PHL}	Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		35	80	ns
		$V_{DD} = 10\text{V}$		25	55	ns
t_{PLH}	Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		35	120	ns
		$V_{DD} = 10\text{V}$		25	65	ns
t_{THL}	Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		65	200	ns
		$V_{DD} = 10\text{V}$		35	115	ns
t_{TLH}	Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		65	300	ns
		$V_{DD} = 10\text{V}$		35	125	ns
C_i	Input Capacitance	Any Input		5.0		pF
CD4023M						
t_{PHL}	Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		50	75	ns
		$V_{DD} = 10\text{V}$		25	40	ns
t_{PLH}	Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		50	75	ns
		$V_{DD} = 10\text{V}$		25	40	ns
t_{THL}	Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		75	125	ns
		$V_{DD} = 10\text{V}$		50	75	ns
t_{TLH}	Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		75	100	ns
		$V_{DD} = 10\text{V}$		40	60	ns
C_i	Input Capacitance	Any Input		5.0		pF
CD4023C						
t_{PHL}	Propagation Delay Time High to Low Level	$V_{DD} = 5.0\text{V}$		50	100	ns
		$V_{DD} = 10\text{V}$		25	50	ns
t_{PLH}	Propagation Delay Time Low to High Level	$V_{DD} = 5.0\text{V}$		50	100	ns
		$V_{DD} = 10\text{V}$		25	50	ns
t_{THL}	Transition Time High to Low Level	$V_{DD} = 5.0\text{V}$		75	150	ns
		$V_{DD} = 10\text{V}$		50	100	ns
t_{TLH}	Transition Time Low to High Level	$V_{DD} = 5.0\text{V}$		75	125	ns
		$V_{DD} = 10\text{V}$		40	75	ns
C_i	Input Capacitance	Any Input		5.0		pF

*AC Parameters are guaranteed by DC correlated testing.